

# MOS Transistor (MOSFET) Device Physics - Quiz

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# MOSFET Device Physics - Quiz ideas

- 1) What does MOSFET stand for?
  - A. Metal Oxide Semiconductor Field Effect Transistor
  - B. Metal Oxide Semiconductor Field Emission Transistor
  - C. Metal Oxide Semiconductor Field Effect Transformer
  - D. Metal Oxide Semiconductor Field Emission Transformer
- 2) Which terminals are part of a MOSFET?
  - A) Source, Drain, Gate, Collector
  - B) Source, Drain, Gate, Emitter
  - C) Source, Drain, Gate, Base
  - D) Source, Drain, Gate, Body
- 3) What is the typical potential of interest in a MOSFET 2D model?
  - A.  $V_{GS}$  and  $I_{DS}$
  - B.  $V_{DS}$  and  $I_{DS}$
  - C.  $V_{GS}$  and  $V_{DS}$
  - D.  $V_{GS}$  and  $V_{BS}$
- 4) In the  $I_D$ - $V_G$  characteristics, what happens when  $V_{GS} > V_T$ ?
  - A. No channel formation
  - B. Channel formation
  - C. Depletion region formation
  - D. Accumulation region formation
- 5) What is the pinch-off point in MOSFET IV characteristics?
  - A. When  $V_{DS} = V_{GS} + V_T$
  - B. When  $V_{DS} = V_{GS} * V_T$
  - C. When  $V_{DS} = V_{GS} - V_T$
  - D. When  $V_{DS} = V_{GS} / V_T$
- 6) What is subthreshold conduction?
  - A. Linear leakage before  $V_T$
  - B. Exponential leakage before  $V_T$
  - C. Exponential leakage after  $V_T$
  - D. Linear leakage after  $V_T$

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7) What is Drain Induced Barrier Lowering (DIBL)?

- A. A short-channel effect where the threshold voltage decreases as the drain voltage increases
- B. A long-channel effect where the threshold voltage decreases as the drain voltage increases
- C. A short-channel effect where the threshold voltage increases as the drain voltage decreases
- D. A long-channel effect where the threshold voltage increases as the drain voltage decreases

8) What is Gate Induced Drain Leakage (GIDL)?

- A. Leakage current when a high electric field is applied to the gate-source overlap region
- B. Leakage current when a high electric field is applied to the drain-source overlap region
- C. Leakage current when a high electric field is applied to the gate-drain overlap region
- D. Leakage current when a high electric field is applied to the gate-body overlap region

9) What is the subthreshold slope (SS)?

- A. The gate voltage required to increase or reduce  $I_{DS}$  by one decade
- B. The drain voltage required to increase or reduce  $I_{DS}$  by one decade
- C. The source voltage required to increase or reduce  $I_{DS}$  by one decade
- D. The body voltage required to increase or reduce  $I_{DS}$  by one decade

10) What happens to the PN junction depletion region width when it is reverse biased?

- A. It decreases
- B. It remains the same
- C. It oscillates
- D. It increases

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